Silicon NPN Power Transistors 2SC5124

DESCRIPTION

·With TO-3PML package
·High voltage switchihg transistor

APPLICATIONS

·Display horizontal deflection output
·Switching regulator and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

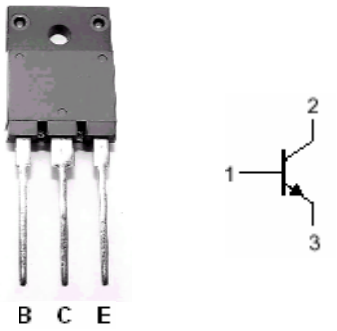

Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		20	A
I_B	Base current		5	A
P_C	Collector power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA; R_{BE}=∞	800			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=8A;I_B=2A			5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=8A;I_B=2A			1.5	V
I_{CBO1}	Collector cut-off current	V_{CB}=1200V; I_E=0			100	μA
I_{CBO2}	Collector cut-off current	V_{CB}=1500V; I_E=0			1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			100	μA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	8			
h_{FE-2}	DC current gain	I_C=8A ; V_{CE}=5V	4		9	
f_T	Transition frequency	I_E=-1A ; V_{CE}=12V		3		MHz
C_{OB}	Output capacitance	V_{CB}=10V;f=1MHz		130		pF
Switching times						
t_{on}	Turn-on time	I_C=6A;I_{B1}=1.2A; I_{B2}=-2.4A R_L=33.3Ω;V_{CC}=200V		0.1		μs
t_{stg}	Storage time			4.0		μs
t_f	Fall time			0.2		μs

PACKAGE OUTLINE

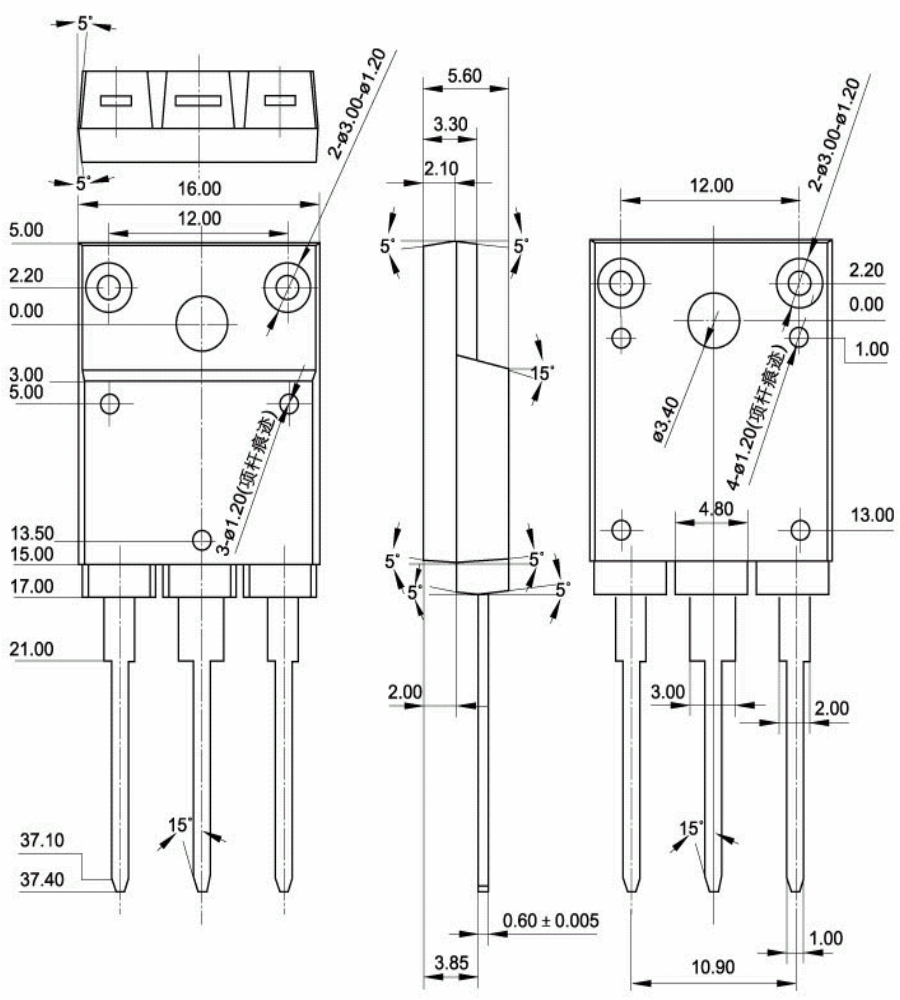

Fig.2 Outline dimensions

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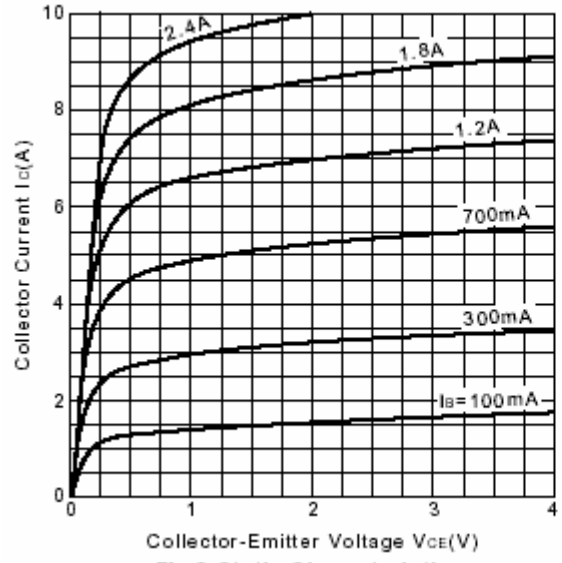

Fig.3 Static Characteristic

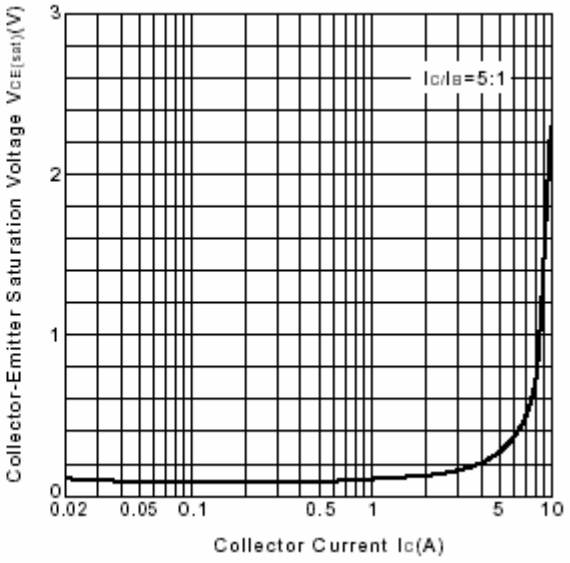

Fig.4 $V_{CE}(sat)$-I_C Characteristics

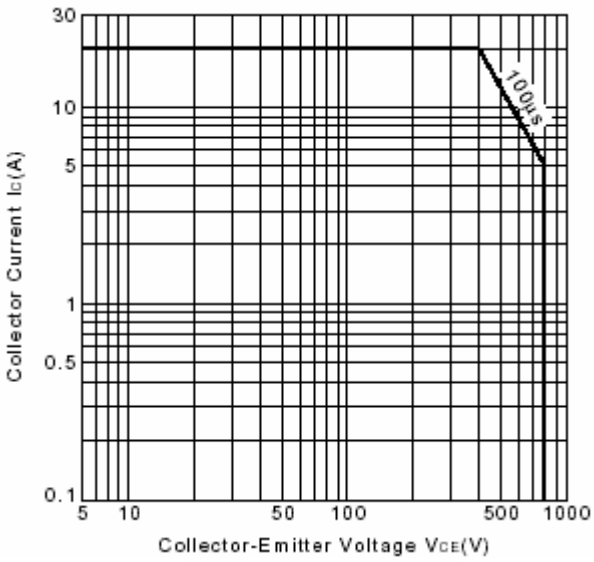

Fig.5 Safe Operating Area

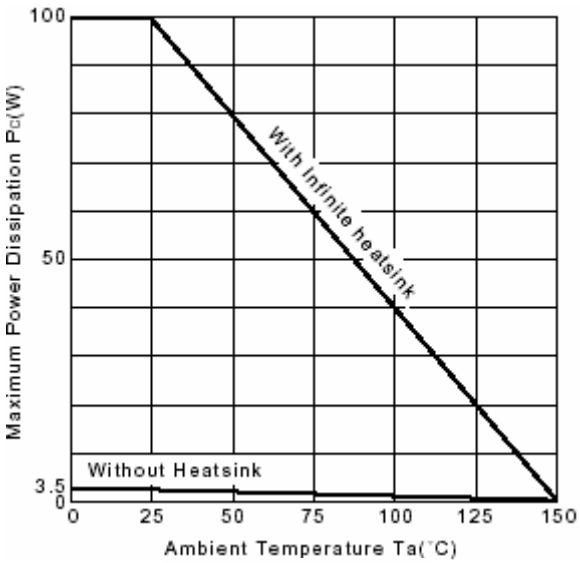

Fig.6 Pc-Ta Derating

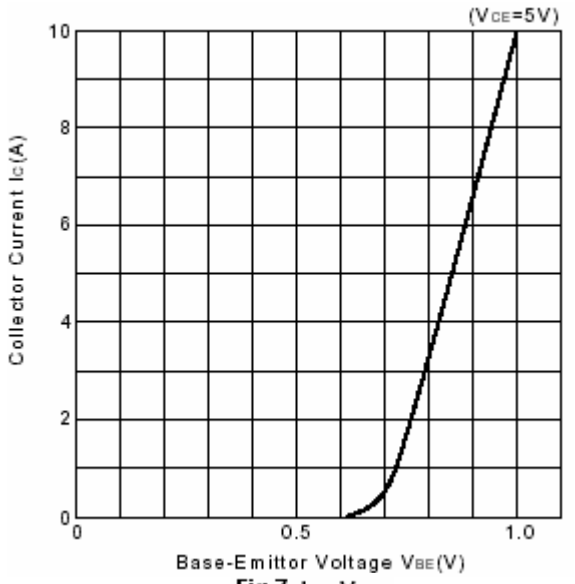

Fig.7 I_C-V_{BE}

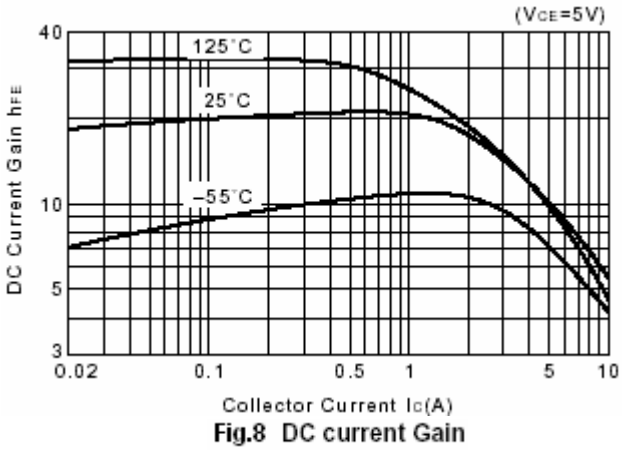

Fig.8 DC current Gain